

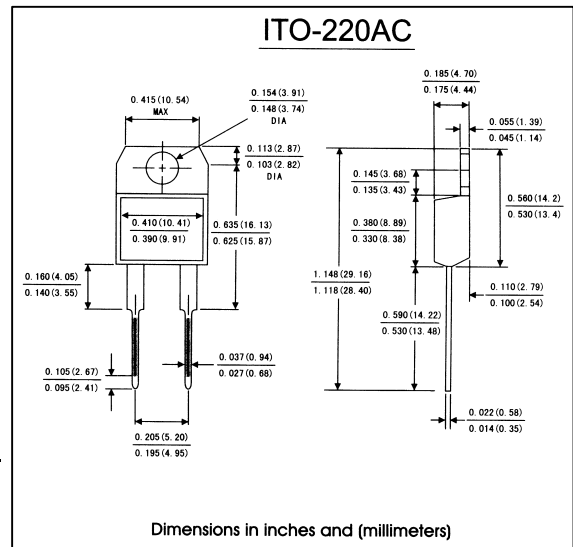
FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Metal silicon junction ,majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss,high efficiency
- High current capability ,Low forward voltage drop
- Single rectifier construction
- High surge capability
- For use in low voltage ,high frequency inverters, free wheeling , and polarity protection applications
- High temperature soldering guaranteed: 250°C/10 seconds

0.25"(6.35mm)from case

MECHANICAL DATA

- Case:** JEDEC DO-220AC molded plastic body
- Terminals:** lead solderable per MIL-STD-750,method 2026
- Polarity:** As marked
- Mounting Position:** Any
- Weight:** 0.08 ounce, 2.24 gram



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified,Single phase,half wave,resistive or inductive)

load. For capacitive load,derate by 20%)

		Symbols	SRF820	SRF830	SRF840	SRF850	SRF860	SRF880	SRF8A0	Units
Maximum repetitive peak reverse voltage		V _{RRM}	20	30	40	50	60	80	100	Volts
Maximum RMS voltage		V _{RMS}	14	21	28	35	42	57	71	Volts
Maximum DC blocking voltage		V _{DC}	20	30	40	50	60	80	100	Volts
Macimum average forward rectified current(see Fig.1)		I _(AV)	8.0							Amps
Repetitive peak forward current(square wavr, 20KHz) at Tc=105℃		I _{FRM}	16.0							Amps
Peak forward surge current 8.3ms singel half sine-wave superimposed on rated load (JEDEC method)		I _{FSM}	150.0							Amps
Maximum instantaneous forward voltage at 7.5 A(Note 1)		V _F	0.65			0.75		0.8	0.85	Volts
Maximum instantaneous reverse current at rated DC blocking voltage(Note 1)	TA=25℃	I _R	1.0							mA
	TA=125℃		15			50				
Typeical thermal resistance(Note 2)		R θ _{JC}	5.0							℃/W
Operating junction temperature range		T _J	-65 to +125			-65 to +150				℃
storage temperature range		T _{STG}	-65 to +150							℃

Notes: 1. Pulse test: 300 μs pulse width,1% duty cycle

2.Thermal resistance from junction to case

RATINGS AND CHARACTERISTIC CURVES SRF820 THRU SRF8A0(SINGLE CHIP)

FIG.1-FORWARD CURRENT DERATING CURVE

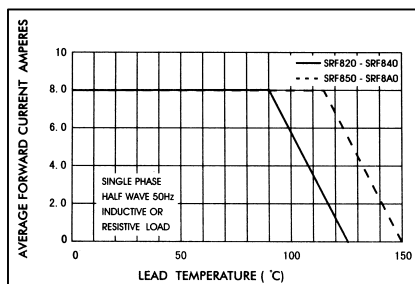


FIG.2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

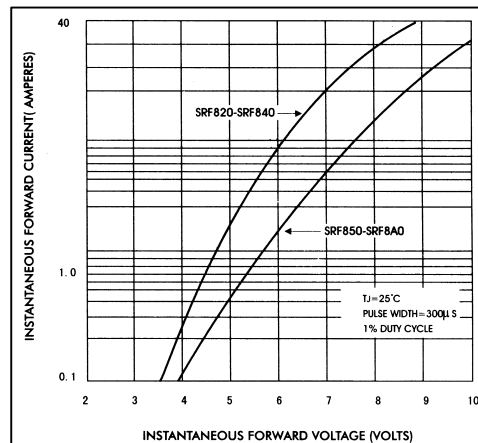


FIG.4-TYPICAL JUNCTION CAPACITANCE

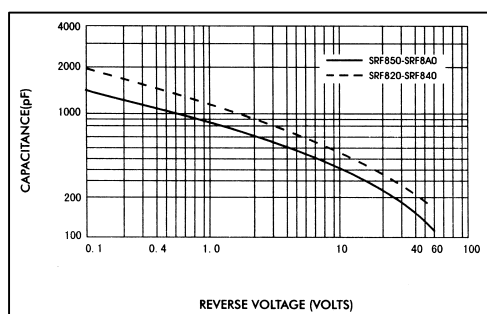


FIG.3-TYPICAL REVERSE CHARACTERISTICS

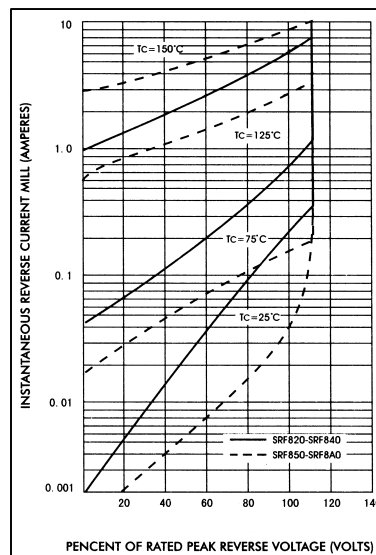


FIG.5-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

